## WHAT IS CLAIMED IS:

1	1. An integrated circuit chip comprising:
2	a substrate, the substrates comprising a plurality of chip structures;
3	a plurality of bonding pads disposed on the substrate, each of the bonding pads
4	being formed from an aluminum bearing material;
5	a surface region formed on each of the bonding pads;
6	an under bump metal layer overlying the surface region;
7	a wetting layer formed overlying the surface region, the wetting layer
8	comprising a plurality of protrusions extending out of the wetting layer and disposed spatially
9	on the wetting layer;
10	a bump layer overlying the wetting layer and mechanically coupling the
11	plurality of protrusions.
1	2. The chip of claim 1 wherein the under bump metal comprises an
2	adhesive material, a wetting material, and a protective material.
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1	3. The chip of claim 1 wherein each of the protrusions has a
2	predetermined height and a predtermined width.
1	4. The chip of claim 1 wherein each of the protrusions has a
2	predetermined height, the height ranging from about 15 to about 20 microns.
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1	5. The chip of claim 1 wherein each of the bonding pads has a dimension
2	of about 80 microns by about 80 microns.
1	6. The chip of claim 1 wherein the wetting layer is provided by a
2	deposition or plating process.
-	deposition of planning process.
1	7. The chip of claim 1 wherein the plurality of protrusions prevents a
2	possibility of the bump layer from peeling from the surface region of the bonding pad.
1	8. The chip of claim 1 wherein the plurality of protrusions prevents a
2	possibility of the bump layer from peeling from the surface region during a reflow process.
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1	9 The chip of claim 1 wherein the substrate comprises silicon

1	10. The chip of claim 1 wherein the substrate is a silicon on insulator
2	wafer.
1	11. A method for fabricating an integrated circuit chip comprising:
2	providing a substrate;
3	forming a plurality of bonding pads overlying the substrate, each of the
4	bonding pads being formed from an aluminum bearing material and including a surface
5	region;
6	forming an under bump metal layer overlying the surface region;
7	forming a wetting layer overlying the under bump metal layer, the wetting
8	layer comprising a plurality of protrusions extending out of the wetting layer and disposed
9	spatially on the wetting layer; and
10	forming a bump layer overlying the wetting layer and mechanically coupling
11	to the plurality of protrusions.
1	12. The method of claim 11 wherein the under bump metrology comprises
2	an adhesive material, a wetting material, and a protective material.
1	13. The method of claim 11 wherein each of the protrusions has a
2	predetermined height and a predtermined width.
1	14. The method of claim 11 wherein each of the protrusions has a
2	predetermined height, the height ranging from about 15 to about 20 microns.
1	15. The method of claim 11 wherein each of the bonding pads has a
2	dimension of about 80 microns by about 80 microns.
1	16. The method of claim 11 wherein the wetting layer is provided by a
2	deposition or plating process.
1	17. The method of claim 11 wherein the plurality of protrusions prevents a
2	possibility of the bump layer from peeling from the surface region of the bonding pad.
1	18. The method of claim 11 further comprising reflowing the bump layer
2	while maintaining the bump layer on the surface region through the plurality of protrusions.